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Kind regards,

Team Nexperia



500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor9 December 2013Product data sheet

### 1. General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X.

### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

### 3. Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

# 4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-	-500	V	
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-400	V	
I <sub>C</sub>	collector current			-	-	-0.25	А	
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C		100	200	-		





#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3
3	В	base	3 2 1 SOT89	sym079

### 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PBHV9040X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89				

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PBHV9040X	%4E

[1] % = placeholder for manufacturing site code

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 8. Limiting values

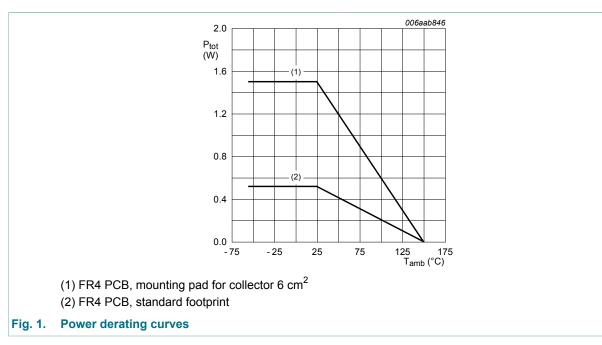
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-500	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-400	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-500	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-0.25	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-0.5	А
I <sub>BM</sub>	peak base current	_		-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



PBHV9040X

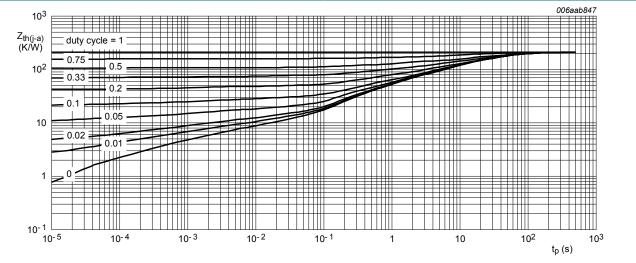
#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 9. Thermal characteristics

Table 6.       Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	240	K/W	
	•		[2]	-	-	83	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W	

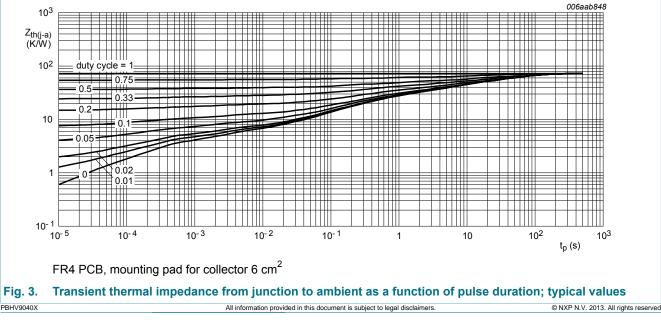
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, standard footprint





#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

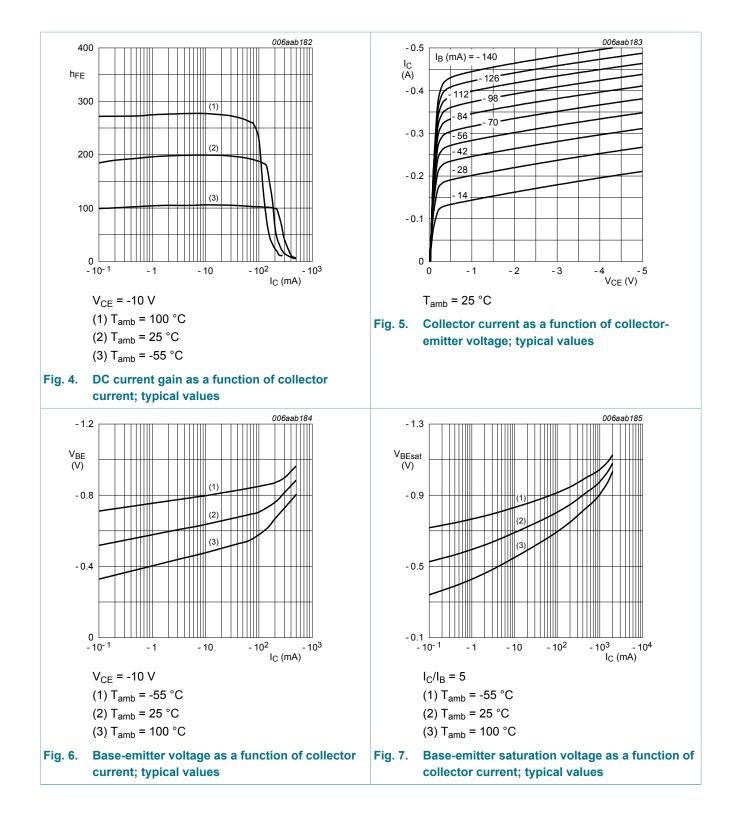
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -320 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C	100	200	-	
		$V_{CE}$ = -10 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	80	200	-	
		$V_{CE}$ = -10 V; I <sub>C</sub> = -250 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	10	25	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -20 mA; $T_{amb}$ = 25 °C	-	-110	-200	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -20 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-1	-1.1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -2 V; I <sub>C</sub> = -0.15 A; I <sub>Bon</sub> = -0.03 A;	-	9	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.03 A; T <sub>amb</sub> = 25 °C	-	1810	-	ns
t <sub>on</sub>	turn-on time		-	1819	-	ns
t <sub>s</sub>	storage time		-	715	-	ns
t <sub>f</sub>	fall time		-	1085	-	ns
t <sub>off</sub>	turn-off time		-	1800	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	55	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	7	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	150	-	pF

### **NXP Semiconductors**

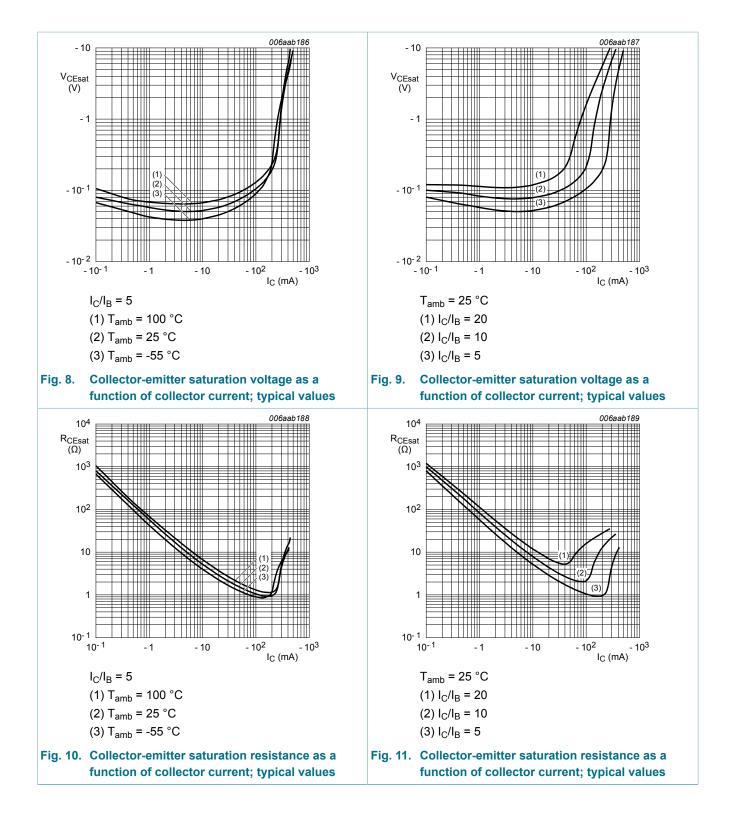
# **PBHV9040X**

#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor



PBHV9040X

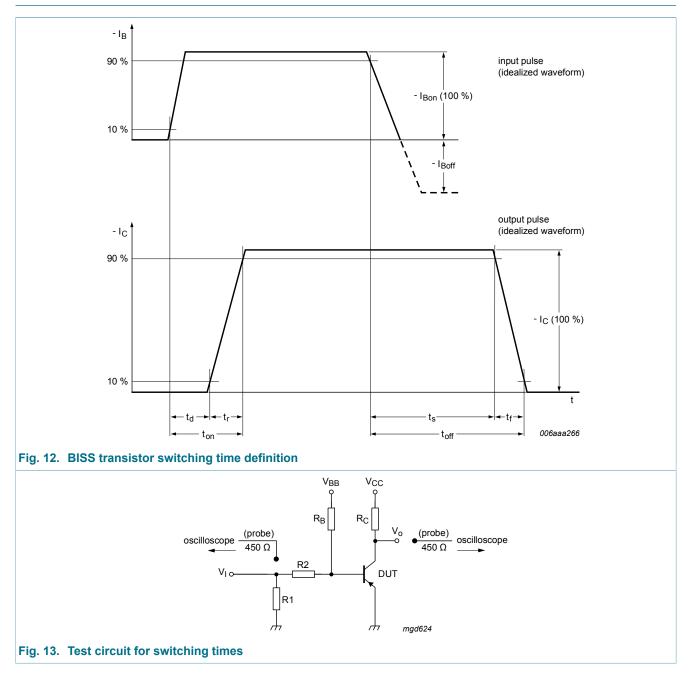
#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor



PBHV9040X

#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 11. Test information



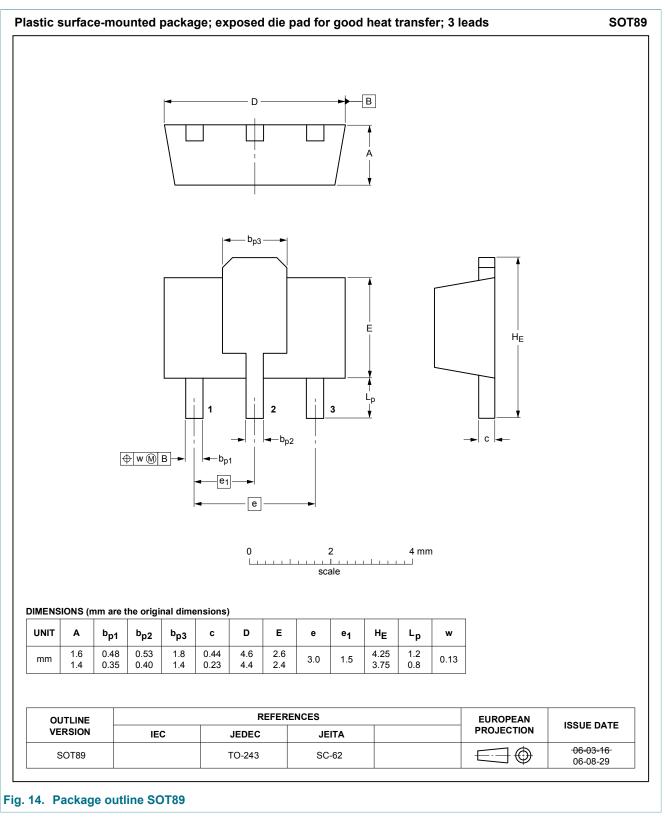
### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PBHV9040X

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 12. Package outline

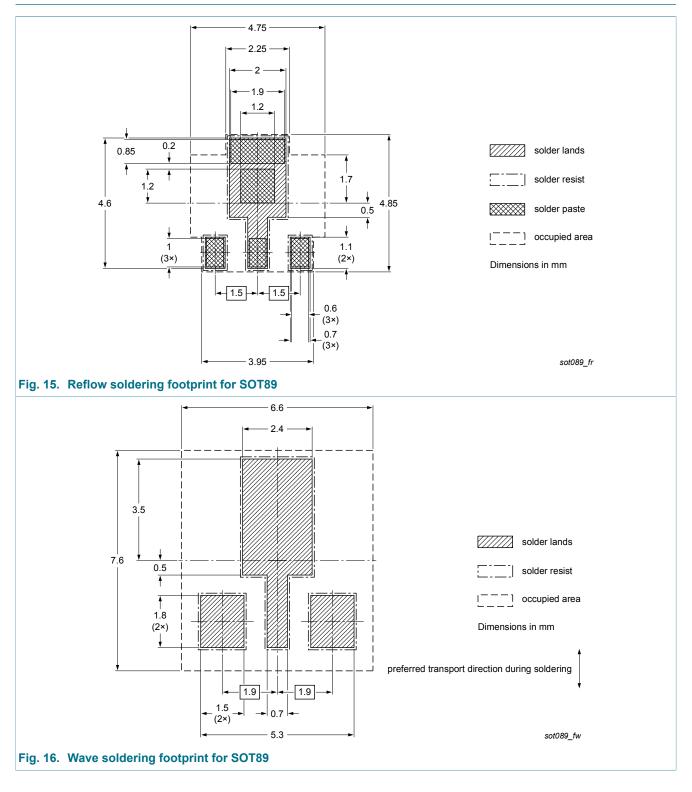


PBHV9040X

Product data sheet

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### 13. Soldering



PBHV9040X

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

# 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV9040X v.1	20131209	Product data sheet	-	-			

#### 500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

### **15. Legal information**

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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9 December 2013

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